

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5352

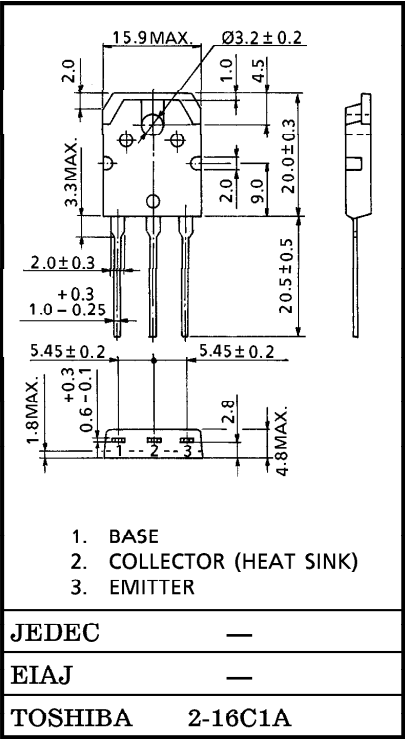
SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS
HIGH SPEED DC-DC CONVERTER APPLICATIONS

- Excellent Switching Times
: $t_r=0.5\mu s$ (Max.), $t_f=0.3\mu s$ (Max.) ($I_C=5A$)
- High Collectors Breakdown Voltage : $V_{CEO}=400V$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	10	A
	Pulse	I_{CP}	15	
Base Current		I_B	5	A
Collector Power Dissipation (Tc=25°C)		P_C	80	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

Unit in mm

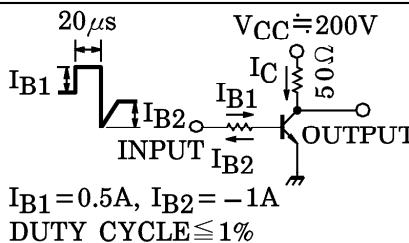


Weight : 4.7g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 480V, I _E = 0	—	—	100	μA
Emitter Cut-off Current		IEBO	V _{EB} = 7V, I _C = 0	—	—	1	mA
Collector-Base Breakdown Voltage		V (BR) CBO	I _C = 1mA, I _E = 0	600	—	—	V
Collector-Emitter Breakdown Voltage		V (BR) CEO	I _C = 10mA, I _B = 0	400	—	—	V
DC Current Gain		h _{FE}	V _{CE} = 5V, I _C = 1A	20	—	—	
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = 4A, I _B = 0.5A	—	—	1.0	V
Base-Emitter Saturation Voltage		V _{BE (sat)}	I _C = 4A, I _B = 0.5A	—	—	1.3	V
Switching Time	Rise Time	t _r	 20 μs V_{CC} = 200V 50 Ω I_{B1} I_{B2} I_C INPUT OUTPUT I_{B1} = 0.5A, I_{B2} = -1A DUTY CYCLE ≤ 1%	—	—	0.5	μs
	Storage Time	t _{stg}		—	—	2.0	
	Fall Time	t _f		—	—	0.3	

